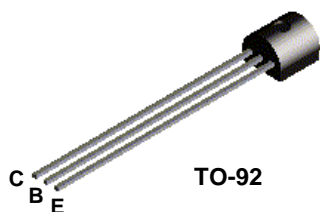
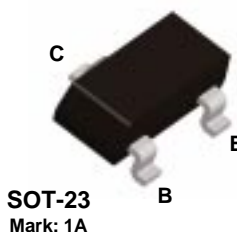


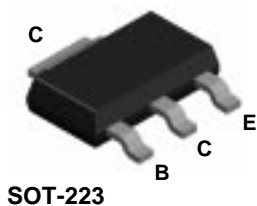
2N3904



MMBT3904



PZT3904



NPN General Purpose Amplifier

This device is designed as a general purpose amplifier and switch. The useful dynamic range extends to 100 mA as a switch and to 100 MHz as an amplifier. Sourced from Process 23.

Absolute Maximum Ratings*

TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
V _{CEO}	Collector-Emitter Voltage	40	V
V _{CB0}	Collector-Base Voltage	60	V
V _{EBO}	Emitter-Base Voltage	6.0	V
I _C	Collector Current - Continuous	200	mA
T _J , T _{stg}	Operating and Storage Junction Temperature Range	-55 to +150	°C

*These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

NOTES:

- 1) These ratings are based on a maximum junction temperature of 150 degrees C.
- 2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

NPN General Purpose Amplifier

(continued)

Electrical Characteristics

TA = 25°C unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Max	Units
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OFF CHARACTERISTICS

$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	$I_C = 1.0 \text{ mA}, I_B = 0$	40		V
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage	$I_C = 10 \mu\text{A}, I_E = 0$	60		V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	$I_E = 10 \mu\text{A}, I_C = 0$	6.0		V
I_{BL}	Base Cutoff Current	$V_{CE} = 30 \text{ V}, V_{EB} = 0$		50	nA
I_{CEX}	Collector Cutoff Current	$V_{CE} = 30 \text{ V}, V_{EB} = 0$		50	nA

ON CHARACTERISTICS*

h_{FE}	DC Current Gain	$I_C = 0.1 \text{ mA}, V_{CE} = 1.0 \text{ V}$ $I_C = 1.0 \text{ mA}, V_{CE} = 1.0 \text{ V}$ $I_C = 10 \text{ mA}, V_{CE} = 1.0 \text{ V}$ $I_C = 50 \text{ mA}, V_{CE} = 1.0 \text{ V}$ $I_C = 100 \text{ mA}, V_{CE} = 1.0 \text{ V}$	40 70 100 60 30	300	
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C = 10 \text{ mA}, I_B = 1.0 \text{ mA}$ $I_C = 50 \text{ mA}, I_B = 5.0 \text{ mA}$		0.2 0.3	V V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	$I_C = 10 \text{ mA}, I_B = 1.0 \text{ mA}$ $I_C = 50 \text{ mA}, I_B = 5.0 \text{ mA}$	0.65	0.85 0.95	V V

SMALL SIGNAL CHARACTERISTICS

f_T	Current Gain - Bandwidth Product	$I_C = 10 \text{ mA}, V_{CE} = 20 \text{ V},$ $f = 100 \text{ MHz}$	300		MHz
C_{obo}	Output Capacitance	$V_{CB} = 5.0 \text{ V}, I_E = 0,$ $f = 1.0 \text{ MHz}$		4.0	pF
C_{ibo}	Input Capacitance	$V_{EB} = 0.5 \text{ V}, I_C = 0,$ $f = 1.0 \text{ MHz}$		8.0	pF
NF	Noise Figure (except MMPQ3904)	$I_C = 100 \mu\text{A}, V_{CE} = 5.0 \text{ V},$ $R_S = 1.0 \text{ k}\Omega, f = 10 \text{ Hz to } 15.7 \text{ kHz}$		5.0	dB

SWITCHING CHARACTERISTICS (except MMPQ3904)

t_d	Delay Time	$V_{CC} = 3.0 \text{ V}, V_{BE} = 0.5 \text{ V},$		35	ns
t_r	Rise Time	$I_C = 10 \text{ mA}, I_{B1} = 1.0 \text{ mA}$		35	ns
t_s	Storage Time	$V_{CC} = 3.0 \text{ V}, I_C = 10 \text{ mA}$		200	ns
t_f	Fall Time	$I_{B1} = I_{B2} = 1.0 \text{ mA}$		50	ns

*Pulse Test: Pulse Width $\leq 300 \mu\text{s}$, Duty Cycle $\leq 2.0\%$

Spice Model

NPN (Is=6.734f Xti=3 Eg=1.11 Vaf=74.03 Bf=416.4 Ne=1.259 Ise=6.734 Ikf=66.78m Xtb=1.5 Br=.7371 Nc=2 Isc=0 Ikr=0 Rc=1 Cjc=3.638p Mjc=.3085 Vjc=.75 Fc=.5 Cje=4.493p Mje=.2593 Vje=.75 Tr=239.5n Tf=301.2p Itf=.4 Vtf=4 Xtf=2 Rb=10)

2N3904 / MMBT3904 / PZT3904

NPN General Purpose Amplifier

(continued)

2N3904 / MMBT3904 / PZT3904

Thermal Characteristics

TA = 25°C unless otherwise noted

Symbol	Characteristic	Max		Units
		2N3904	*PZT3904	
P _D	Total Device Dissipation	625	1,000	mW
	Derate above 25°C	5.0	8.0	mW/°C
R _{θJC}	Thermal Resistance, Junction to Case	83.3		°C/W
R _{θJA}	Thermal Resistance, Junction to Ambient	200	125	°C/W

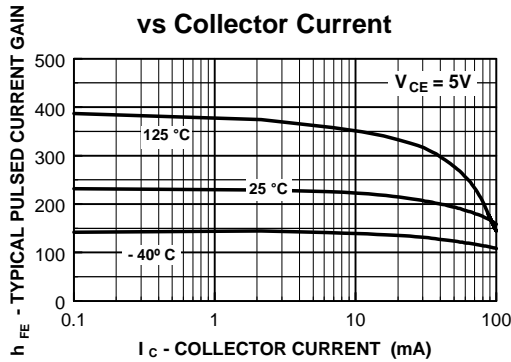
Symbol	Characteristic	Max		Units
		**MMBT3904	MMPQ3904	
P _D	Total Device Dissipation	350	1,000	mW
	Derate above 25°C	2.8	8.0	mW/°C
R _{θJA}	Thermal Resistance, Junction to Ambient Effective 4 Die Each Die	357		°C/W
			125	°C/W
			240	°C/W

* Device mounted on FR-4 PCB 36 mm X 18 mm X 1.5 mm; mounting pad for the collector lead min. 6 cm².

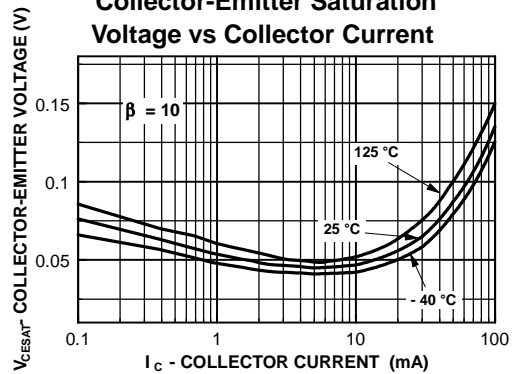
** Device mounted on FR-4 PCB 1.6" X 1.6" X 0.06."

Typical Characteristics

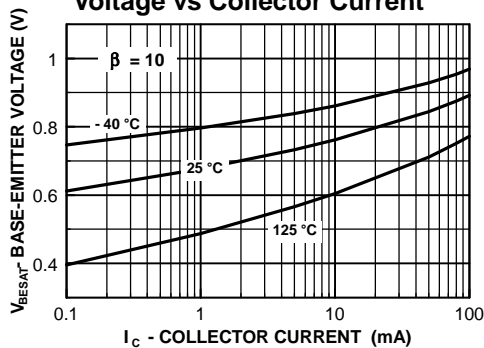
Typical Pulsed Current Gain vs Collector Current



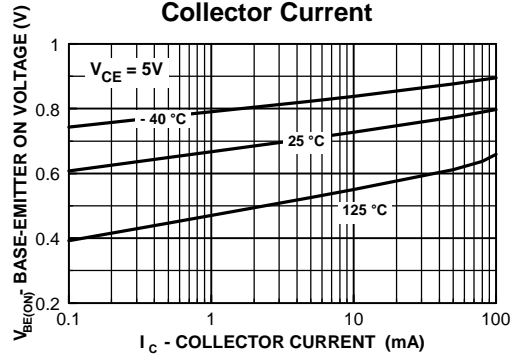
Collector-Emitter Saturation Voltage vs Collector Current



Base-Emitter Saturation Voltage vs Collector Current



Base-Emitter ON Voltage vs Collector Current



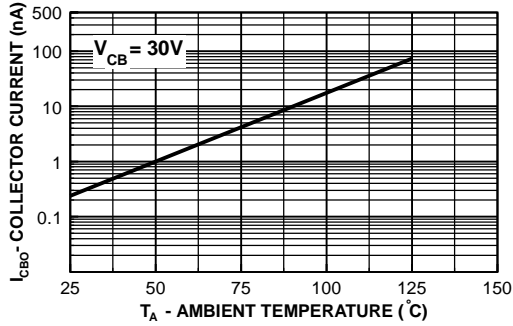
NPN General Purpose Amplifier

(continued)

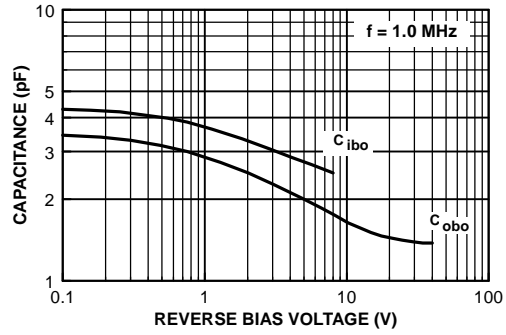
2N3904 / MMBT3904 / PZT3904

Typical Characteristics (continued)

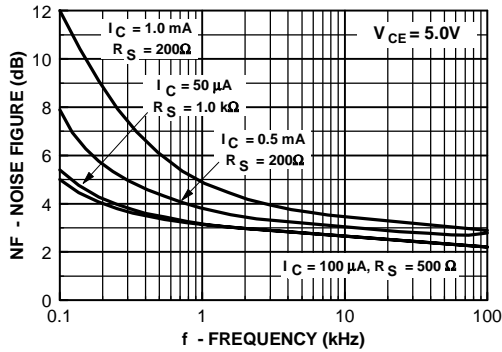
Collector-Cutoff Current vs Ambient Temperature



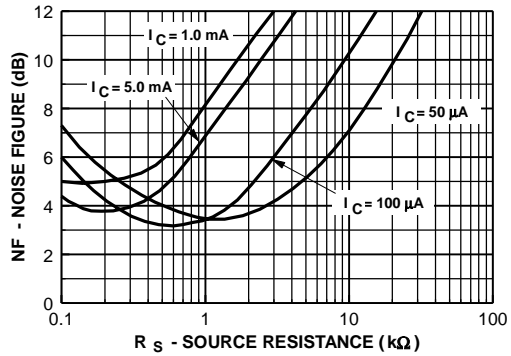
Capacitance vs Reverse Bias Voltage



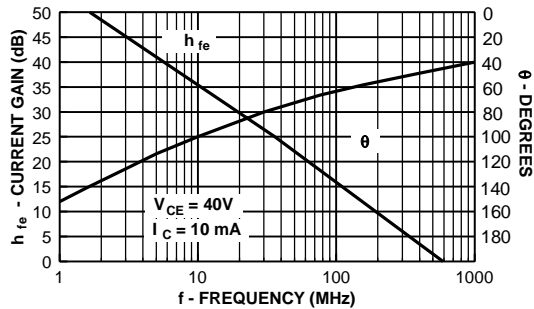
Noise Figure vs Frequency



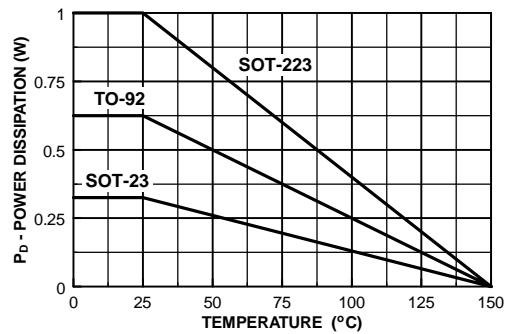
Noise Figure vs Source Resistance



Current Gain and Phase Angle vs Frequency

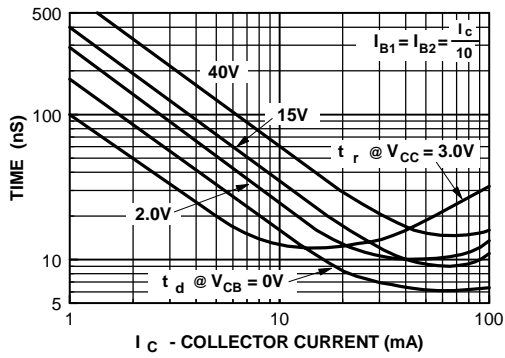


Power Dissipation vs Ambient Temperature

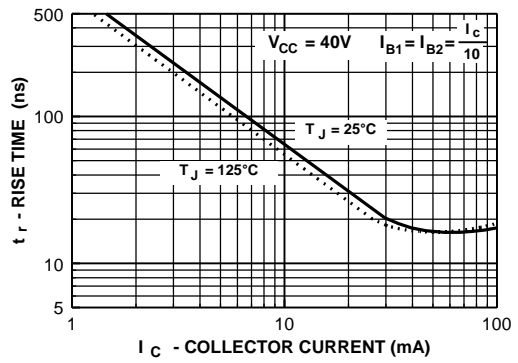


Typical Characteristics (continued)

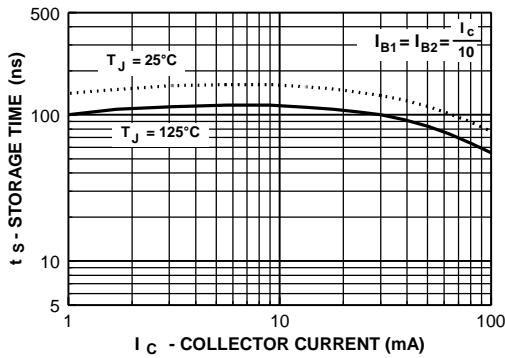
Turn-On Time vs Collector Current



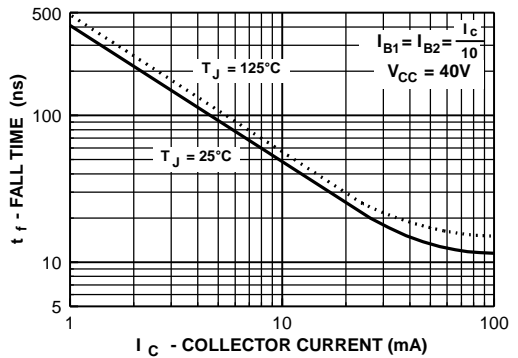
Rise Time vs Collector Current



Storage Time vs Collector Current



Fall Time vs Collector Current



Test Circuits

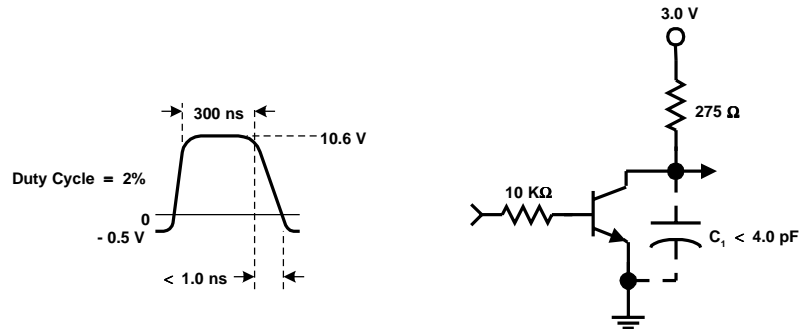


FIGURE 1: Delay and Rise Time Equivalent Test Circuit

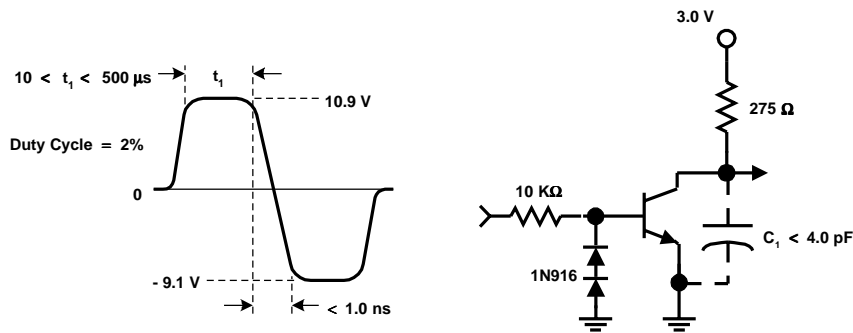


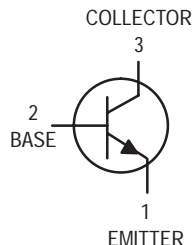
FIGURE 2: Storage and Fall Time Equivalent Test Circuit

General Purpose Transistors

NPN Silicon

2N3903
2N3904*

*Motorola Preferred Device



CASE 29-04, STYLE 1
TO-92 (TO-226AA)

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector–Emitter Voltage	V_{CEO}	40	Vdc
Collector–Base Voltage	V_{CBO}	60	Vdc
Emitter–Base Voltage	V_{EBO}	6.0	Vdc
Collector Current — Continuous	I_C	200	mAdc
Total Device Dissipation @ $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D	625 5.0	mW mW/ $^\circ\text{C}$
Total Device Dissipation @ $T_C = 25^\circ\text{C}$ Derate above 25°C	P_D	1.5 12	Watts mW/ $^\circ\text{C}$
Operating and Storage Junction Temperature Range	T_J, T_{stg}	-55 to +150	$^\circ\text{C}$

THERMAL CHARACTERISTICS(1)

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	200	$^\circ\text{C}/\text{W}$
Thermal Resistance, Junction to Case	$R_{\theta JC}$	83.3	$^\circ\text{C}/\text{W}$

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
----------------	--------	-----	-----	------

OFF CHARACTERISTICS

Collector–Emitter Breakdown Voltage (2) ($I_C = 1.0 \text{ mAdc}, I_B = 0$)	$V_{(BR)CEO}$	40	—	Vdc
Collector–Base Breakdown Voltage ($I_C = 10 \mu\text{Adc}, I_E = 0$)	$V_{(BR)CBO}$	60	—	Vdc
Emitter–Base Breakdown Voltage ($I_E = 10 \mu\text{Adc}, I_C = 0$)	$V_{(BR)EBO}$	6.0	—	Vdc
Base Cutoff Current ($V_{CE} = 30 \text{ Vdc}, V_{EB} = 3.0 \text{ Vdc}$)	I_{BL}	—	50	nAdc
Collector Cutoff Current ($V_{CE} = 30 \text{ Vdc}, V_{EB} = 3.0 \text{ Vdc}$)	I_{CEX}	—	50	nAdc

1. Indicates Data in addition to JEDEC Requirements.
2. Pulse Test: Pulse Width $\leq 300 \mu\text{s}$; Duty Cycle $\leq 2.0\%$.

Preferred devices are Motorola recommended choices for future use and best overall value.

REV 2

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FACT™	QS™
FACT Quiet Series™	Quiet Series™
FAST®	SuperSOT™-3
FASTr™	SuperSOT™-6
GTO™	SuperSOT™-8
HiSeC™	TinyLogic™

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Definition of Terms

Datasheet Identification	Product Status	Definition
Advance Information	Formative or In Design	This datasheet contains the design specifications for product development. Specifications may change in any manner without notice.
Preliminary	First Production	This datasheet contains preliminary data, and supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
No Identification Needed	Full Production	This datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
Obsolete	Not In Production	This datasheet contains specifications on a product that has been discontinued by Fairchild semiconductor. The datasheet is printed for reference information only.

2N3903 2N3904

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted) (Continued)

Characteristic	Symbol	Min	Max	Unit
ON CHARACTERISTICS				
DC Current Gain ⁽¹⁾ ($I_C = 0.1 \text{ mAdc}$, $V_{CE} = 1.0 \text{ Vdc}$)	h_{FE}	20	—	—
	2N3903	40	—	
	2N3904			
($I_C = 1.0 \text{ mAdc}$, $V_{CE} = 1.0 \text{ Vdc}$)		35	—	
	2N3903	70	—	
	2N3904			
($I_C = 10 \text{ mAdc}$, $V_{CE} = 1.0 \text{ Vdc}$)		50	150	
	2N3903	100	300	
	2N3904			
($I_C = 50 \text{ mAdc}$, $V_{CE} = 1.0 \text{ Vdc}$)		30	—	
	2N3903	60	—	
	2N3904			
($I_C = 100 \text{ mAdc}$, $V_{CE} = 1.0 \text{ Vdc}$)		15	—	
	2N3903	30	—	
	2N3904			
Collector–Emitter Saturation Voltage ⁽¹⁾ ($I_C = 10 \text{ mAdc}$, $I_B = 1.0 \text{ mAdc}$) ($I_C = 50 \text{ mAdc}$, $I_B = 5.0 \text{ mAdc}$)	$V_{CE(sat)}$	—	0.2	Vdc
		—	0.3	
Base–Emitter Saturation Voltage ⁽¹⁾ ($I_C = 10 \text{ mAdc}$, $I_B = 1.0 \text{ mAdc}$) ($I_C = 50 \text{ mAdc}$, $I_B = 5.0 \text{ mAdc}$)	$V_{BE(sat)}$	0.65	0.85	Vdc
		—	0.95	

SMALL–SIGNAL CHARACTERISTICS

Current–Gain — Bandwidth Product ($I_C = 10 \text{ mAdc}$, $V_{CE} = 20 \text{ Vdc}$, $f = 100 \text{ MHz}$)	f_T	250	—	MHz
		300	—	
Output Capacitance ($V_{CB} = 5.0 \text{ Vdc}$, $I_E = 0$, $f = 1.0 \text{ MHz}$)	C_{obo}	—	4.0	pF
Input Capacitance ($V_{EB} = 0.5 \text{ Vdc}$, $I_C = 0$, $f = 1.0 \text{ MHz}$)	C_{ibo}	—	8.0	pF
Input Impedance ($I_C = 1.0 \text{ mAdc}$, $V_{CE} = 10 \text{ Vdc}$, $f = 1.0 \text{ kHz}$)	h_{ie}	1.0	8.0	k Ω
		1.0	10	
Voltage Feedback Ratio ($I_C = 1.0 \text{ mAdc}$, $V_{CE} = 10 \text{ Vdc}$, $f = 1.0 \text{ kHz}$)	h_{re}	0.1	5.0	$\times 10^{-4}$
		0.5	8.0	
Small–Signal Current Gain ($I_C = 1.0 \text{ mAdc}$, $V_{CE} = 10 \text{ Vdc}$, $f = 1.0 \text{ kHz}$)	h_{fe}	50	200	—
		100	400	
Output Admittance ($I_C = 1.0 \text{ mAdc}$, $V_{CE} = 10 \text{ Vdc}$, $f = 1.0 \text{ kHz}$)	h_{oe}	1.0	40	μmhos
Noise Figure ($I_C = 100 \mu\text{Adc}$, $V_{CE} = 5.0 \text{ Vdc}$, $R_S = 1.0 \text{ k } \Omega$, $f = 1.0 \text{ kHz}$)	NF	—	6.0	dB
		—	5.0	

SWITCHING CHARACTERISTICS

Delay Time	$(V_{CC} = 3.0 \text{ Vdc}$, $V_{BE} = 0.5 \text{ Vdc}$, $I_C = 10 \text{ mAdc}$, $I_{B1} = 1.0 \text{ mAdc}$)	t_d	—	35	ns
Rise Time		t_r	—	35	ns
Storage Time	$(V_{CC} = 3.0 \text{ Vdc}$, $I_C = 10 \text{ mAdc}$, $I_{B1} = I_{B2} = 1.0 \text{ mAdc}$)	t_s	—	175	ns
Fall Time		t_f	—	50	ns

1. Pulse Test: Pulse Width $\leq 300 \mu\text{s}$; Duty Cycle $\leq 2.0\%$.

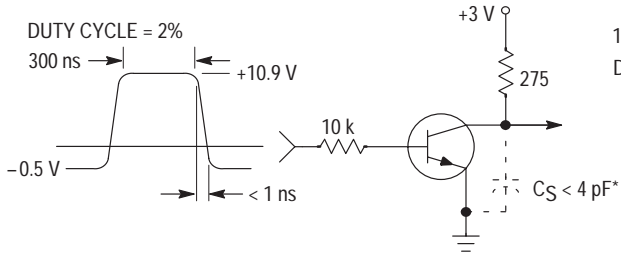


Figure 1. Delay and Rise Time Equivalent Test Circuit

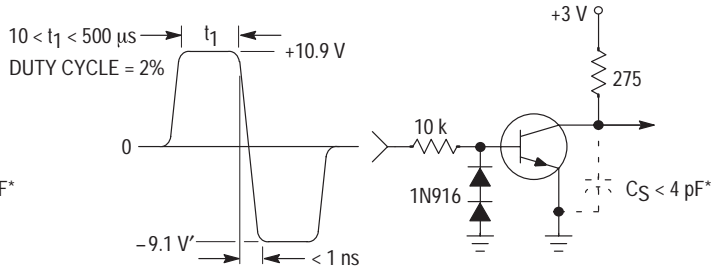


Figure 2. Storage and Fall Time Equivalent Test Circuit

* Total shunt capacitance of test jig and connectors

TYPICAL TRANSIENT CHARACTERISTICS

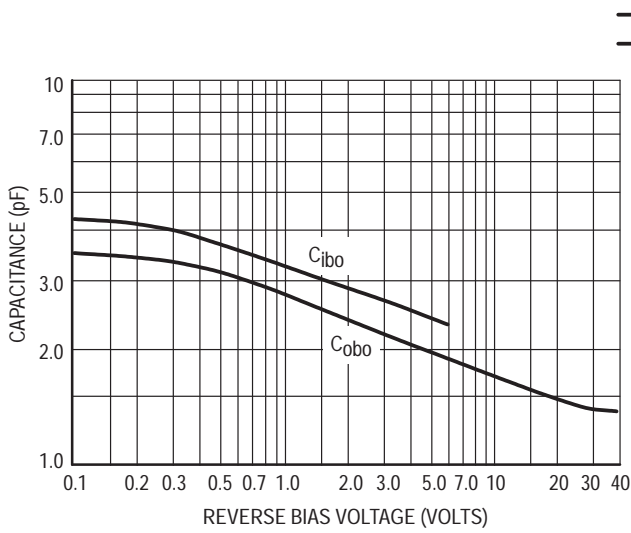


Figure 3. Capacitance

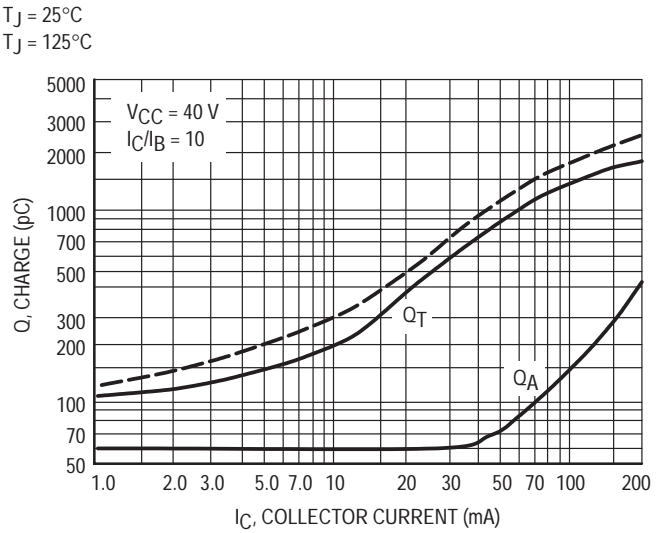


Figure 4. Charge Data

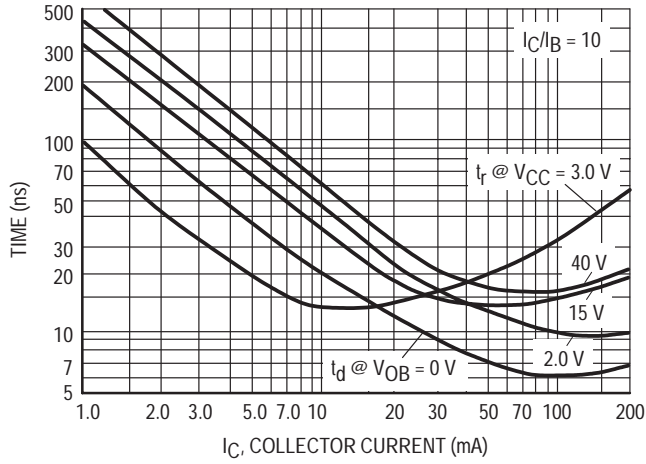


Figure 5. Turn-On Time

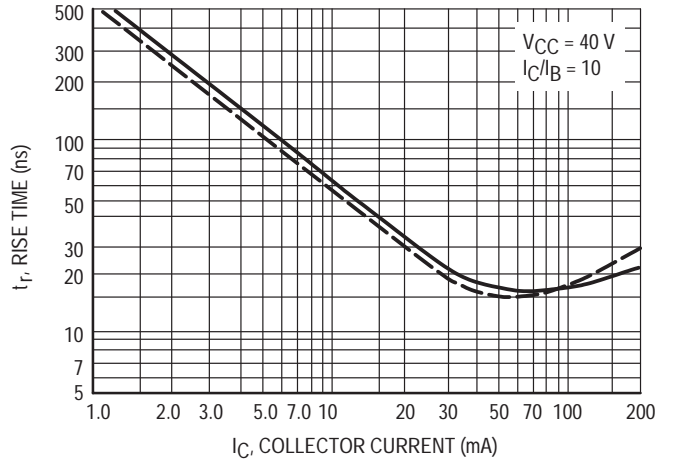


Figure 6. Rise Time

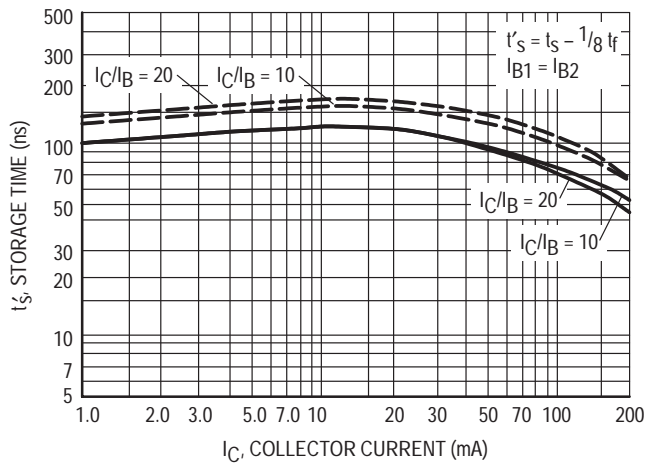


Figure 7. Storage Time

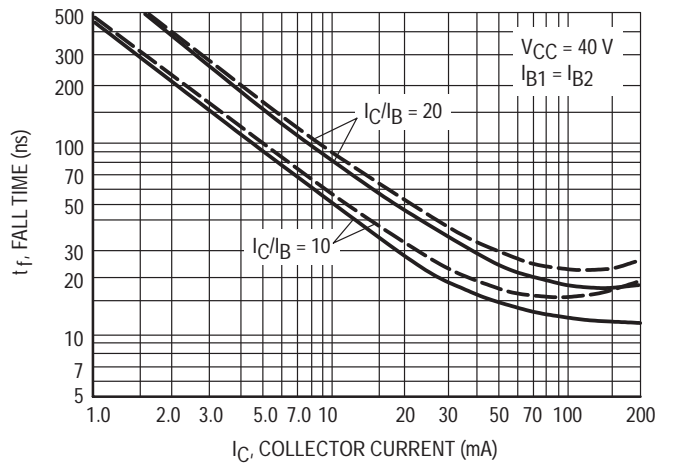


Figure 8. Fall Time

TYPICAL AUDIO SMALL-SIGNAL CHARACTERISTICS
NOISE FIGURE VARIATIONS

(VCE = 5.0 Vdc, TA = 25°C, Bandwidth = 1.0 Hz)

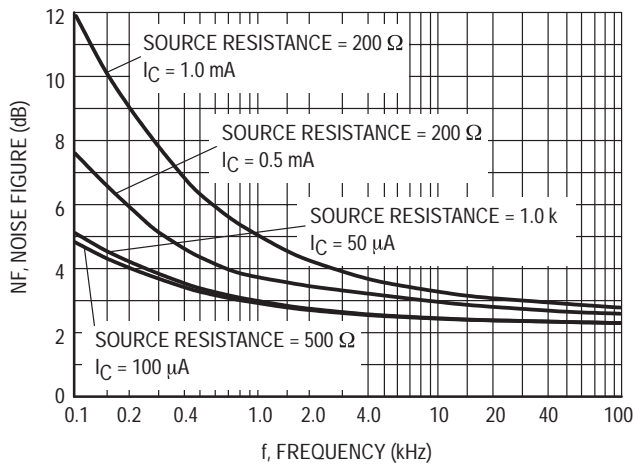


Figure 9.

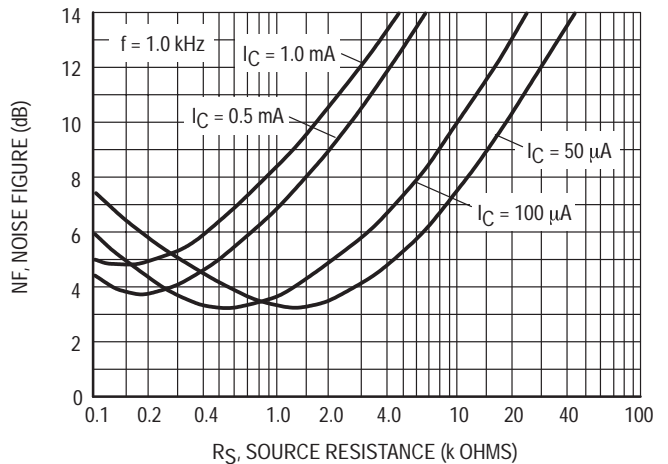


Figure 10.

h PARAMETERS

($V_{CE} = 10 \text{ Vdc}$, $f = 1.0 \text{ kHz}$, $T_A = 25^\circ\text{C}$)

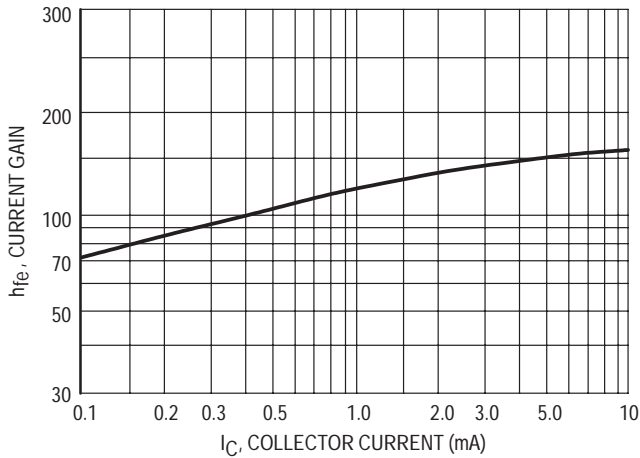


Figure 11. Current Gain

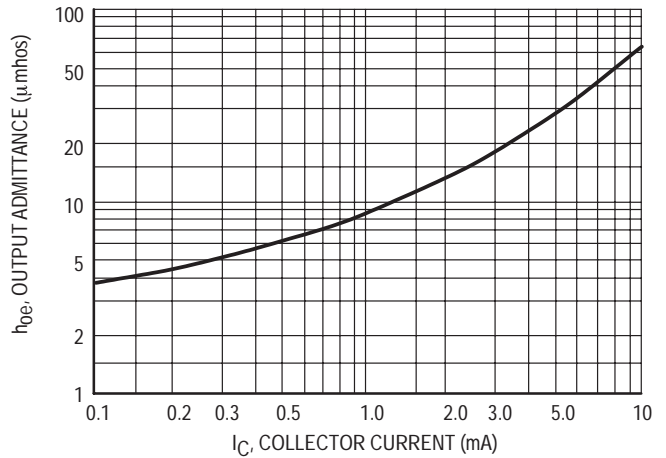


Figure 12. Output Admittance

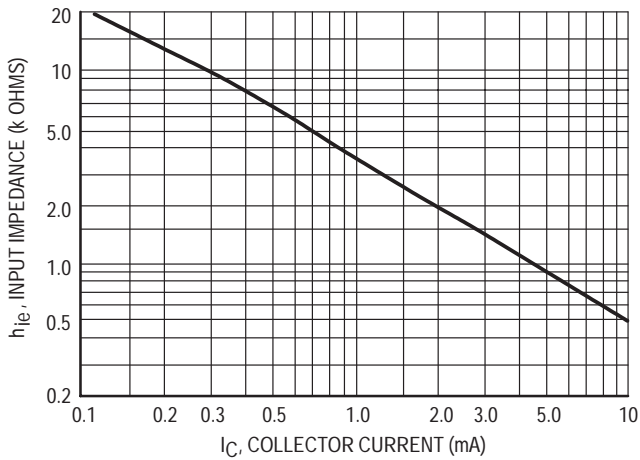


Figure 13. Input Impedance

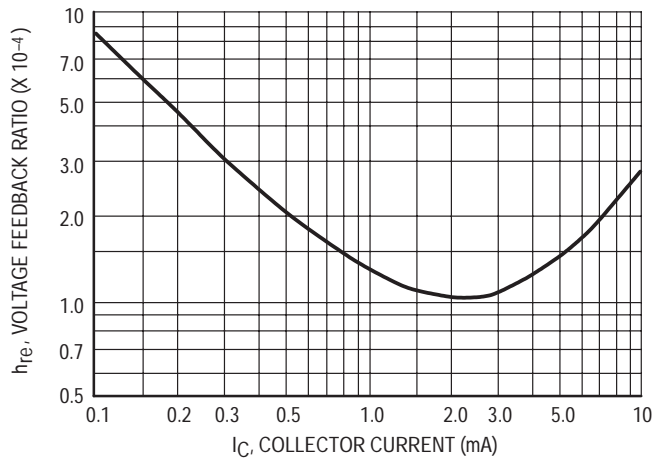


Figure 14. Voltage Feedback Ratio

TYPICAL STATIC CHARACTERISTICS

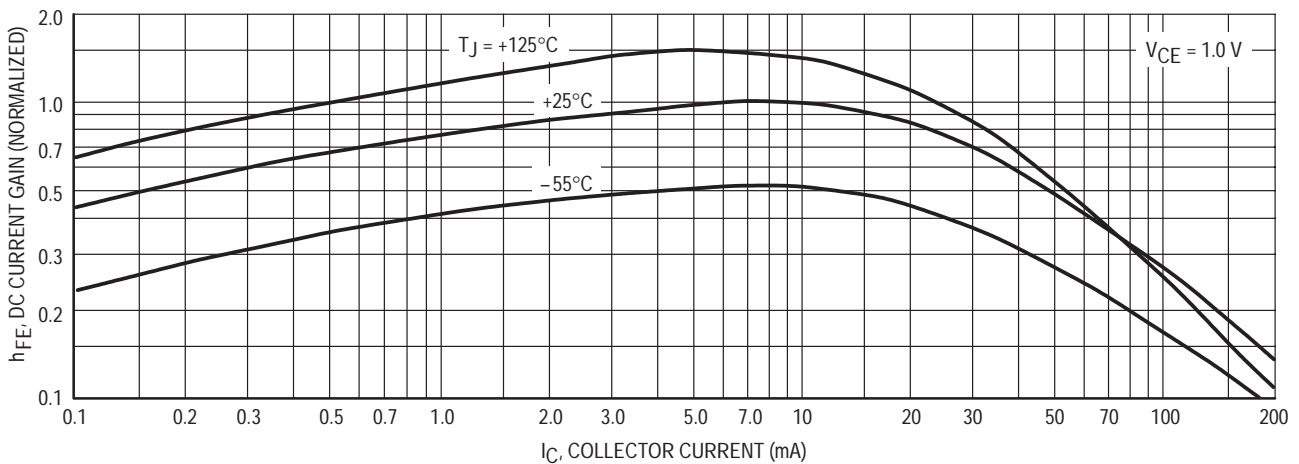


Figure 15. DC Current Gain

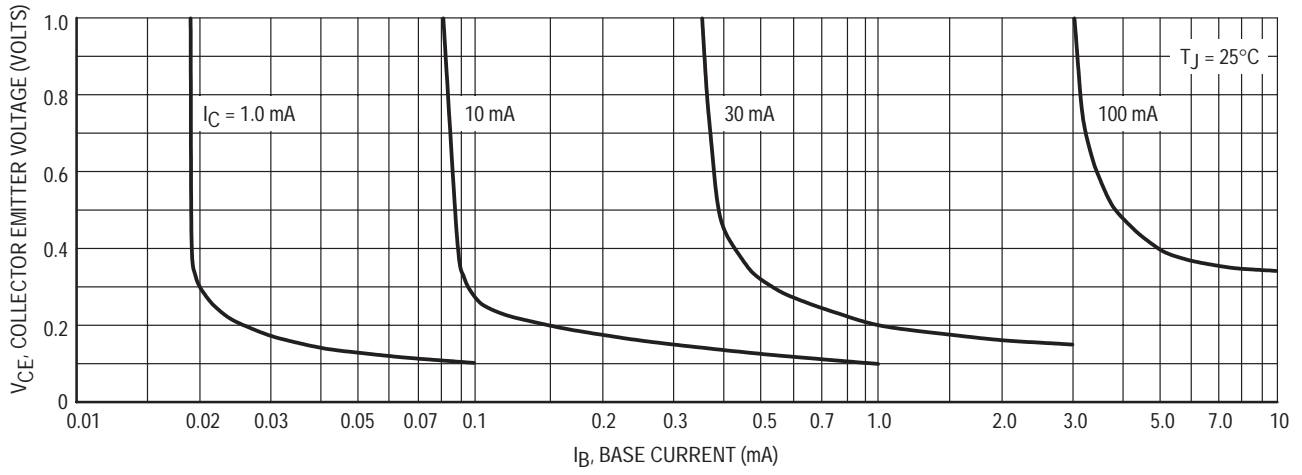


Figure 16. Collector Saturation Region

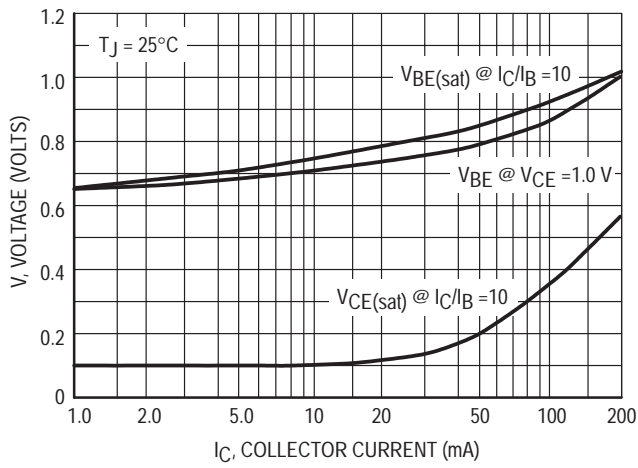


Figure 17. "ON" Voltages

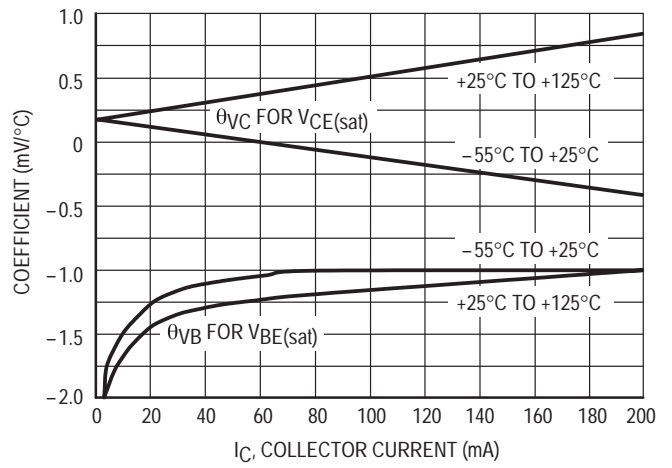
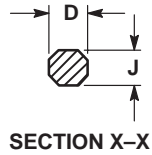
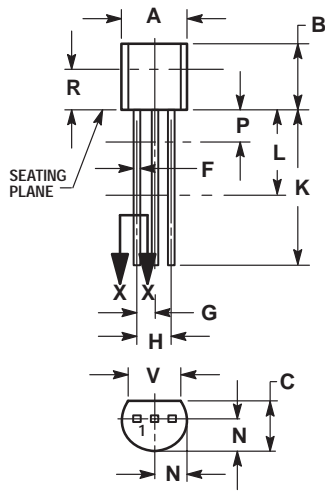


Figure 18. Temperature Coefficients

PACKAGE DIMENSIONS



SECTION X-X

**CASE 029-04
(TO-226AA)
ISSUE AD**


NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED.
4. DIMENSION F APPLIES BETWEEN P AND L. DIMENSION D AND J APPLY BETWEEN L AND K. MINIMUM LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.175	0.205	4.45	5.20
B	0.170	0.210	4.32	5.33
C	0.125	0.165	3.18	4.19
D	0.016	0.022	0.41	0.55
F	0.016	0.019	0.41	0.48
G	0.045	0.055	1.15	1.39
H	0.095	0.105	2.42	2.66
J	0.015	0.020	0.39	0.50
K	0.500	---	12.70	---
L	0.250	---	6.35	---
N	0.080	0.105	2.04	2.66
P	---	0.100	---	2.54
R	0.115	---	2.93	---
V	0.135	---	3.43	---

STYLE 1:

- PIN 1. EMITTER
2. BASE
3. COLLECTOR

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How to reach us:

USA/EUROPE/Locations Not Listed: Motorola Literature Distribution;
P.O. Box 5405; Denver, Colorado 80217. 1-800-441-2447

MFAX: RMFAX0@email.sps.mot.com – TOUCHTONE 602-244-6609
INTERNET: <http://Design-NET.com>

JAPAN: Nippon Motorola Ltd.; Tatsumi-SPD-JLDC, 6F Seibu-Butsuryu-Center,
3-14-2 Tatsumi Koto-Ku, Tokyo 135, Japan. 81-3-3521-8315

ASIA/PACIFIC: Motorola Semiconductors H.K. Ltd.; 8B Tai Ping Industrial Park,
51 Ting Kok Road, Tai Po, N.T., Hong Kong. 852-26629298



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